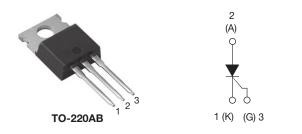
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Thyristor High Voltage, Phase Control SCR, 25 A



| PRIMARY CHARACTERISTICS | | | | | | | |
|------------------------------------|-------------------|--|--|--|--|--|--|
| I _{T(AV)} | 16 A | | | | | | |
| V _{DRM} /V _{RRM} | 1200 V | | | | | | |
| V _{TM} | 1.25 V | | | | | | |
| I _{GT} | 45 mA | | | | | | |
| TJ | -40 °C to +125 °C | | | | | | |
| Package | TO-220AB | | | | | | |
| Circuit configuration | Single SCR | | | | | | |

FEATURES

- Easy control peak current at charger power up to reduce passive / electromechanical components
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power **FREE** rectification
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV/HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS | | | | | | | | |
|--|----|----|---|--|--|--|--|--|
| APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS | | | | | | | | |
| Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W | 18 | 22 | А | | | | | |

| MAJOR RATINGS AND CHARACTERISTICS | | | | | | | |
|------------------------------------|------------------------------|-------------|------|--|--|--|--|
| PARAMETER | VALUES | UNITS | | | | | |
| I _{T(AV)} | Sinusoidal waveform | 16 | ٨ | | | | |
| I _{RMS} | | 25 | A | | | | |
| V _{RRM} /V _{DRM} | | 1200 | V | | | | |
| I _{TSM} | | 320 | А | | | | |
| V _T | 16 A, T _J = 25 °C | 1.25 | V | | | | |
| dV/dt | | 500 | V/µs | | | | |
| dl/dt | | 150 | A/µs | | | | |
| TJ | | -40 to +125 | °C | | | | |

| VOLTAGE RATINGS | | | |
|-----------------|---|--|---|
| PART NUMBER | V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V | V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V | I _{RRM} /I _{DRM} AT 125 °C mA |
| VS-25TTS12HM3 | 1200 | 1200 | 10 |

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 1
 Document Number: 96530

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COMPLIANT

VS-25TTS12HM3



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| ABSOLUTE MAXIMUM RATING | S | | | | | | | |
|---|----------------------------------|--|---|------|--------------------|------------------|--|--|
| PARAMETER | SYMBOL | TEST CO | | VAL | UES | UNITS | | |
| FARAMETER | SYMBOL TEST CONDITIONS | | | TYP. | MAX. | | | |
| Maximum average on-state current | I _{T(AV)} | $T_{\rm C}$ = 93 °C, 180° conduc | tion half sine wave | 1 | 6 | | | |
| Maximum RMS on-state current | I _{RMS} | | | 2 | 5 | А | | |
| Maximum peak, one-cycle, | | 10 ms sine pulse, rated V | / _{RRM} applied | 2 | 70 | ~ | | |
| non-repetitive surge current | I _{TSM} | 10 ms sine pulse, no vol | tage reapplied | 32 | 20 | 1 | | |
| Maximum I ² t for fusing | l ² t | 10 ms sine pulse, rated V | / _{RRM} applied | 36 | 65 | A ² s | | |
| Maximum 1-t for fusing | 1-1 | 10 ms sine pulse, no vol | 515 | | - A ² S | | | |
| Maximum I²√t for fusing | l²√t | t = 0.1 to 10 ms, no voltage reapplied | | | 52 | A²√s | | |
| Maximum on-state voltage drop | V _{TM} | 16 A, T _J = 25 °C | | 1.25 | | V | | |
| On-state slope resistance | r _t | T, = 125 °C | | 12 | 2.0 | mΩ | | |
| Threshold voltage | V _{T(TO)} | $V_{T(TO)}$ 1 1. | | .0 | V | | | |
| Maximum reverse and direct leakage | I _{BM} /I _{DM} | T _J = 25 °C | $V_{\rm R}$ = rated $V_{\rm RRM}/V_{\rm DRM}$ | 0 | .5 | | | |
| current | 'RM/ 'DM | T _J = 125 °C | VR - Taleu VRRM/ VDRM | 1 | 0 | | | |
| Holding current | Ι _Η | Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$ | | - | 150 | mA | | |
| Maximum latching current | ١L | Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$ | | | 00 | | | |
| Maximum rate of rise of off-state voltage | dV/dt | $T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = open$ | | | 00 | V/µs | | |
| Maximum rate of rise of turned-on current | dl/dt | | | 150 | | A∕µs | | |

| TRIGGERING | | | | | | | | |
|--|--------------------|--|--------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | |
| Maximum peak gate power | P _{GM} | | 8.0 | W | | | | |
| Maximum average gate power | P _{G(AV)} | | 2.0 | vv | | | | |
| Maximum peak positive gate current | +I _{GM} | | 1.5 | А | | | | |
| Maximum peak negative gate voltage | -V _{GM} | | 10 | V | | | | |
| | | Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$ | 60 | | | | | |
| Maximum required DC gate current to trigger | I _{GT} | Anode supply = 6 V, resistive load, $T_J = 25 \degree C$ | 45 | mA | | | | |
| | | Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$ | 20 | | | | | |
| | | Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$ | 2.5 | | | | | |
| Maximum required DC gate voltage to trigger | V _{GT} | Anode supply = 6 V, resistive load, $T_J = 25 \degree C$ | 2.0 | | | | | |
| voltage to trigger | | Anode supply = 6 V, resistive load, $T_J = 125 \degree C$ | 1.0 | V | | | | |
| Maximum DC gate voltage not to trigger | V _{GD} | | 0.25 | | | | | |
| Maximum DC gate current not to trigger | I _{GD} | T _J = 125 °C, V _{DRM} = rated value | 2.0 | mA | | | | |

| SWITCHING | | | | |
|-------------------------------|-----------------|-------------------------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Typical turn-on time | t _{gt} | T _J = 25 °C | 0.9 | |
| Typical reverse recovery time | t _{rr} | T ₁ = 125 °C | 4 | μs |
| Typical turn-off time | tq | 1j = 125 C | 110 | |

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VS-25TTS12HM3

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| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|---------|-----------------------------------|--------------------------------------|------------|------------|--|--|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | |
| Maximum junction and storage temperature range | | T _J , T _{Stg} | | -40 to 125 | °C | | | |
| Maximum thermal resistance, junction to case | | R _{thJC} | DC operation | 1.1 | | | | |
| Maximum thermal resistance, junction to ambient | | R _{thJA} | | 62 | °C/W | | | |
| Typical thermal resistance, case to heatsink | | R _{thCS} | Mounting surface, smooth and greased | 0.5 | | | | |
| Approximate weight | | | | 2 | g | | | |
| Approximate weight | | | | 0.07 | oz. | | | |
| Mounting torque | minimum | | | 6 (5) | kgf∙cm | | | |
| | maximum | | | 12 (10) | (lbf ⋅ in) | | | |
| Marking device | | | Case style TO-220AB | 25TT | S12H | | | |

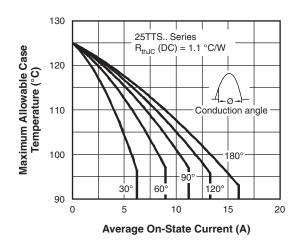


Fig. 1 - Current Rating Characteristics

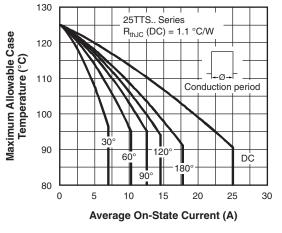


Fig. 2 - Current Rating Characteristics

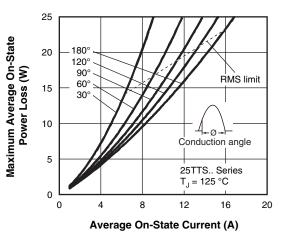


Fig. 3 - On-State Power Loss Characteristics

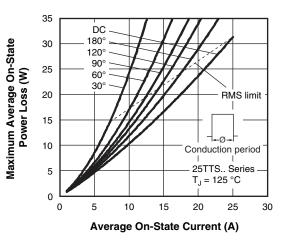


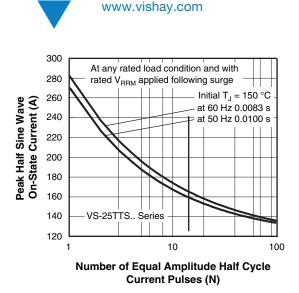
Fig. 4 - On-State Power Loss Characteristics

3

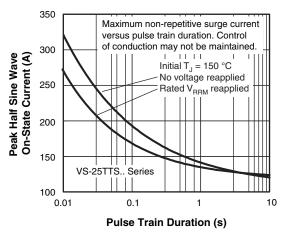
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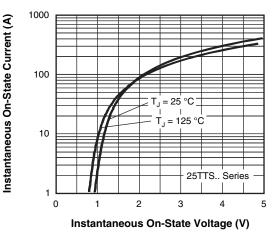














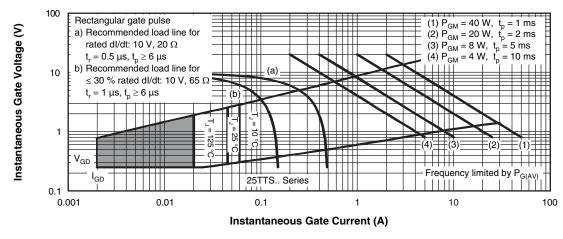


Fig. 8 - Gate Characteristics

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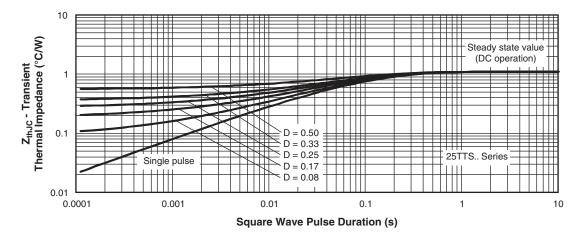
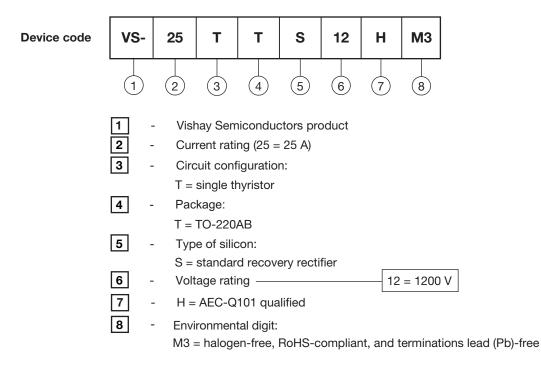


Fig. 9 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

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| ORDERING INFORMATION (Example) | | | | | | | | |
|--------------------------------|------------------|------------------------|--------------------------|--|--|--|--|--|
| PREFERRED P/N | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | | |
| VS-25TTS12HM3 | 50 | 1000 | Antistatic plastic tubes | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|--|
| Dimensions www.vishay.com/doc?95222 | | | | | | |
| Part marking information | www.vishay.com/doc?95028 | | | | | |

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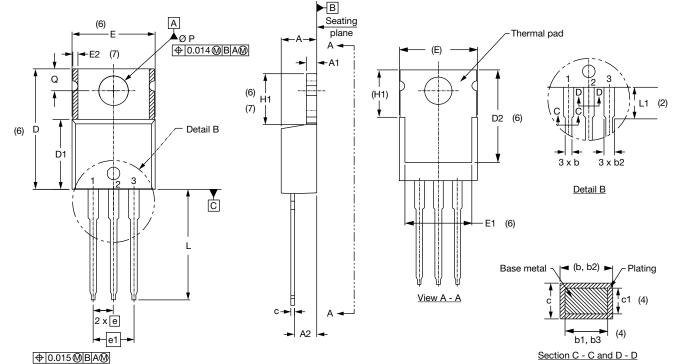
Outline Dimensions



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Conforms to JEDEC[®] outline TO-220AB

| SYMBOL | MILLIN | IETERS | INC | HES | NOTES | SYMBOL | MILLIN | IETERS | INC | HES | NOTES | |
|--------|--------|--------|-------|-------|-------|----------|--------|--------|-------|-------|-------|------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | | STIVIDUL | MIN. | MAX. | MIN. | MAX. | NOTES | |
| А | 4.25 | 4.65 | 0.167 | 0.183 | | | D2 | 11.68 | 12.88 | 0.460 | 0.507 | 6 |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | | | E | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| A2 | 2.56 | 2.92 | 0.101 | 0.115 | | | E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| b | 0.69 | 1.01 | 0.027 | 0.040 | | | E2 | - | 0.76 | - | 0.030 | 7 |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 | | е | 2.41 | 2.67 | 0.095 | 0.105 | |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | | | e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | H1 | 5.84 | 6.86 | 0.230 | 0.270 | 6, 7 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | | | L | 13.52 | 14.02 | 0.532 | 0.552 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 | | L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| D | 14.85 | 15.25 | 0.585 | 0.600 | 3 | | ØР | 3.54 | 3.73 | 0.139 | 0.147 | |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | | | Q | 2.60 | 3.00 | 0.102 | 0.118 | |

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

(8) Outline conforms to JEDEC[®] TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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